

15. (Once Amended) A field emitter display device, comprising:
at least one emitter having [a] an implantation layer that releases electrons at a predetermined energy level, wherein the layer lowers the potential barrier to enhance the releasing of electrons and the layer limits the outgassing so as to inhibit degradation of the at least one emitter.
16. (Once Amended) The device of claim 15, wherein the implantation layer is embedded under [in] the surface of the at least one emitter.
17. (Once Amended) A field emitter display device, comprising:
at least one emitter having [a] an implantation layer that releases electrons at a predetermined energy level, wherein the implantation layer affects the image force so as to enhance the releasing of electrons and the implantation layer limits the outgassing so as to inhibit degradation of the at least one emitter.
18. (Once Amended) The device of claim 17, wherein the implantation layer is embedded in the surface of the at least one emitter.
19. (Once Amended) A field emitter display device, comprising:
at least one emitter having [a] an implantation layer that emits electrons at a predetermined energy level, wherein the layer improves the Schottky effect so as to enhance the emission of electrons and the implantation layer limits the outgassing so as to inhibit degradation of the at least one emitter.
20. (Once Amended) The device of claim 19, wherein the implantation layer is embedded [in] under the surface of the at least one emitter.
21. (Once Amended) A field emitter display device, comprising:
at least one emitter having [a] an implantation layer that releases electrons at a predetermined energy level, wherein the implantation layer decreases the dielectric effect of the

at least one emitter to enhance the releasing of electrons and the implantation layer limits the outgassing so as to inhibit degradation of the at least one emitter.

22. (Once Amended) The device of claim 21, wherein the implantation layer is embedded in the surface of the at least one emitter.

23. (Once Amended) A field emitter display device, comprising:
at least one emitter having a silicon oxide ion implantation layer.

24. (Once Amended) A field emitter display device, comprising:
at least one emitter having an oxide implantation layer that releases electrons at a predetermined energy level.